

Features

- · Split Gate Trench MOSFET Technology
- Low R_{DS(on)} & FOM
- Low C_{rss}
- Extremely Low Switching Loss
- · Excellent Stability and Uniformity
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)
- · Moisture Sensitivity Level 1

Maximum Ratings

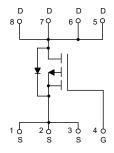
- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 20°C/W Junction to Ambient(t≤10S)⁽²⁾
- Thermal Resistance: 50°C/W Junction to Ambient(Steady-State) (2)
- Thermal Resistance: 1.04°C/W Junction to Case(Steady-State) (2)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	-60	V
Gate-Source Volltage	V _{GS}	±18	V
Continuous Drain Current	I _D	-80	Α
Pulsed Drain Current (3)	I _{DM}	-320	Α
Total Power Dissipation ⁽⁴⁾	P _D	120	W
Single Pulsed Avalanche Energy ⁽⁵⁾	E _{AS}	400	mJ

Note:

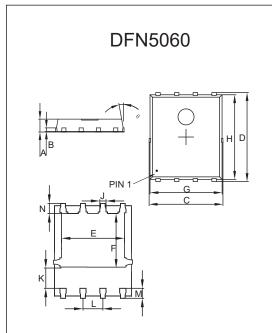
- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C . The Power dissipation P_{DSM} is based on $R_{\theta JA}$ t≤ 10s and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design.
- 3. Repetitive rating; pulse width limited by max. junction temperature.
- 4. P_D is based on max. junction temperature, using junction-case thermal resistance.
- 5. V_{DD} =-60V, R_G =25 Ω , L=2mH, I_{AS} =20A.

Internal Structure and Marking Code





P-CHANNEL MOSFET



DIMENSIONS						
DIM	INCHES		MM		NOTE	
DIIVI	MIN	MAX	MIN	MAX	NOTE	
Α	0.031	0.047	0.80	1.20		
В	0.010		0.254		TYP.	
С	0.193	0.222	4.90	5.64		
D	0.232	0.250	5.90	6.35		
Е	0.148	0.167	3.75	4.25		
F	0.126	0.154	3.20	3.92		
G	0.189	0.213	4.80	5.40		
Н	0.222	0.239	5.65	6.06		
K	0.045	0.059	1.15	1.50		
J	0.012	0.020	0.30	0.50		
L	0.046	0.054	1.17	1.37		
М	0.012	0.028	0.30	0.71		
N	0.016	0.028	0.40	0.71		

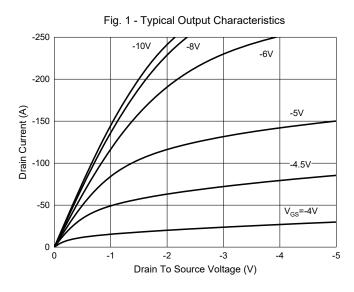


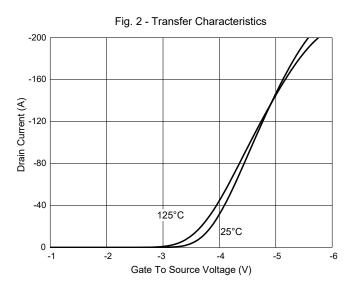
Electrical Characteristics @ 25°C (Unless Otherwise Specified)

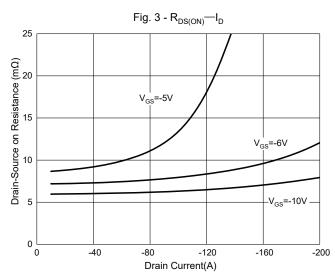
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics					1		
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250μA	-60			V	
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±18V			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V			-1	μA	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=-250\mu A$	-2	-2.7	-4	V	
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-20A		6.1	8	mΩ	
Gate Resistance	R _g	Drain open, f=1Mhz		21		Ω	
Diode Characteristics			·				
Continuous Body Diode Current	Is				-80	Α	
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-20A			-1.3	V	
Reverse Recovery Time	t _{rr}	1 - 201 dildt-E001/us		46		ns	
Reverse Recovery Charge	Q _{rr}	I _S =-20A,di/dt=500A/μs		153		nC	
Dynamic Characteristics							
Input Capacitance	C _{iss}			5450			
Output Capacitance	C _{oss}	V_{DS} =-30V, V_{GS} =0V,f=1MHz		900		pF	
Reverse Transfer Capacitance	C _{rss}			65			
Total Gate Charge	Qg			82			
Gate-Source Charge	Q _{gs}	V _{DS} =-30V,V _{GS} =-10V,I _D =-20A		24		nC	
Gate-Drain Charge	Q_{gd}			16.6			
Turn-On Delay Time	t _{d(on)}			12.8			
Turn-On Rise Time	t _r	V _{DS} =-30V, V _{GS} =-10V,		48		no	
Turn-Off Delay Time	t _{d(off)}	$R_G=1.6\Omega, I_D=-20A$		134.1		ns	
Turn-Off Fall Time	t _f			155.6			

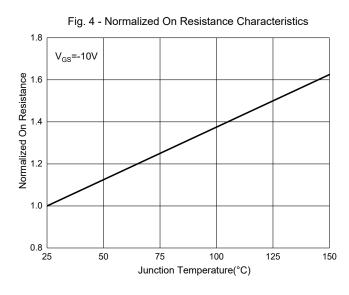


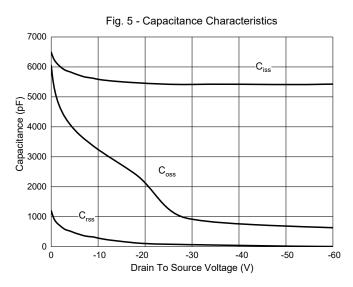
Curve Characteristics

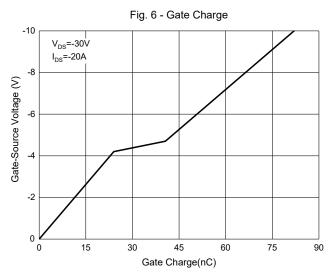






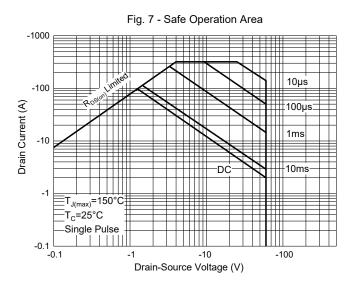








Curve Characteristics



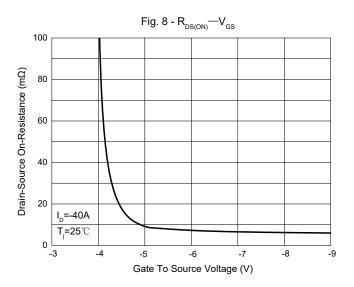
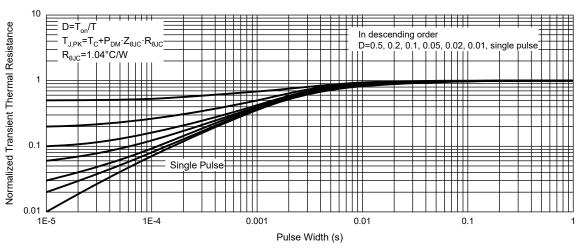


Fig. 9 - Normalized Transient Thermal Impedance



Rev.3-4-09022022 4/5 MCCSEMI.COM



Ordering Information

Device	Packing	
Part Number-TP	Tape&Reel: 5Kpcs/Reel	

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